SITRI

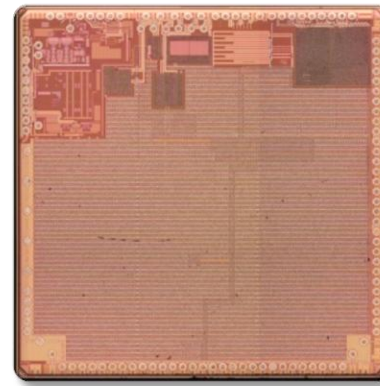
www.sitrigroup.com

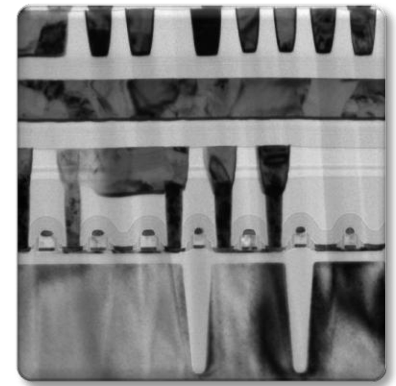
Weibo

Wechat

CXD5603

GNSS Receiver（Fully-Depleted Silicon-On-Insulator）





Product Analysis Report

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